

NTD50N03R-35G-VB Datasheet

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (m Ω)	I_D (A)	Q_g (Typ.)
30	7 at $V_{GS} = 10$ V	50	19 nC
	9 at $V_{GS} = 4.5$ V	45	

FEATURES

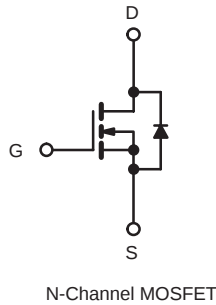
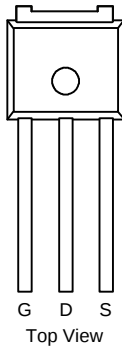
- Halogen-free
- Trench Gen III Power MOSFET
- 100 % R_g Tested
- 100 % UIS Tested


RoHS
 COMPLIANT

APPLICATIONS

- DC/DC Conversion
- System Power

TO-251



ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	$T_C = 25^\circ\text{C}$	I_D	50	A
	$T_C = 70^\circ\text{C}$		45	
	$T_A = 25^\circ\text{C}$		14 ^{b, c}	
	$T_A = 70^\circ\text{C}$		10 ^{b, c}	
Pulsed Drain Current		I_{DM}	150	
Avalanche Current		I_{AS}	25	mJ
Avalanche Energy		E_{AS}	40	
Continuous Source-Drain Diode Current	$T_C = 25^\circ\text{C}$	I_S	15	A
	$T_A = 25^\circ\text{C}$		2.9 ^{b, c}	
	$T_C = 25^\circ\text{C}$		28	W
Maximum Power Dissipation	$T_C = 70^\circ\text{C}$	P_D	18	
	$T_A = 25^\circ\text{C}$		3.5 ^{b, c}	
	$T_A = 70^\circ\text{C}$		2.2 ^{b, c}	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature)			260	

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient	$t \leq 10$ s	R_{thJA}	29	36	$^\circ\text{C/W}$
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	3.6	4.5	

Notes:

- Based on $T_C = 25^\circ\text{C}$.
- Surface Mounted on 1" x 1" FR4 board.
- $t = 10$ s.

SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	30			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		33		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 5		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.2		3.0	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			1	μA
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C			5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	15			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 10 A		7		mΩ
		V _{GS} = 4.5 V, I _D = 7 A		9		
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 10 A		24		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		1700		pF
Output Capacitance	C _{oss}			200		
Reverse Transfer Capacitance	C _{rss}			150		
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 10 A		33		nC
Gate-Source Charge	Q _{gs}	V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 10 A		18		
Gate-Drain Charge	Q _{gd}			7.3		
Gate Resistance	R _g			6.2		
Gate Resistance	R _g	f = 1 MHz	0.2	0.8	1.6	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 4.5 V, R _g = 1 Ω		15	30	ns
Rise Time	t _r			12	24	
Turn-Off Delay Time	t _{d(off)}			13	26	
Fall Time	t _f			10	20	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω		9	18	
Rise Time	t _r			9	18	
Turn-Off Delay Time	t _{d(off)}			14	28	
Fall Time	t _f			8	16	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			16	A
Pulse Diode Forward Current	I _{SM}				32	
Body Diode Voltage	V _{SD}	I _S = 3 A, V _{GS} = 0 V		0.78	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 10 A, dI/dt = 100 A/μs, T _J = 25 °C		17	34	ns
Body Diode Reverse Recovery Charge	Q _{rr}			9.5	19	nC
Reverse Recovery Fall Time	t _a			10		ns
Reverse Recovery Rise Time	t _b			7		

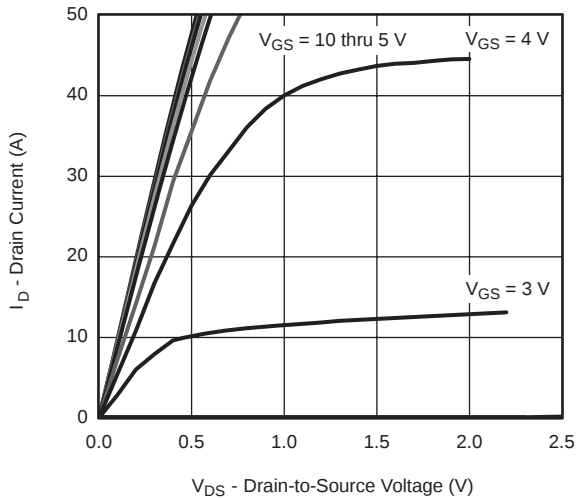
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

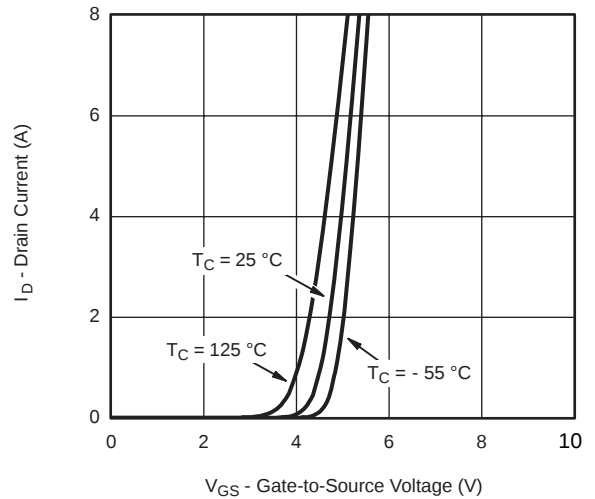
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

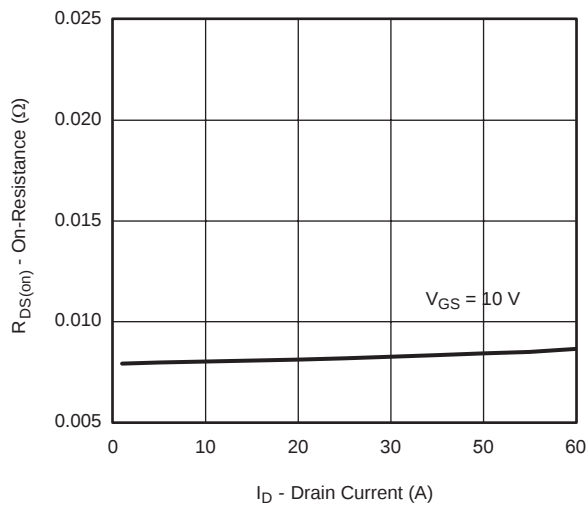
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



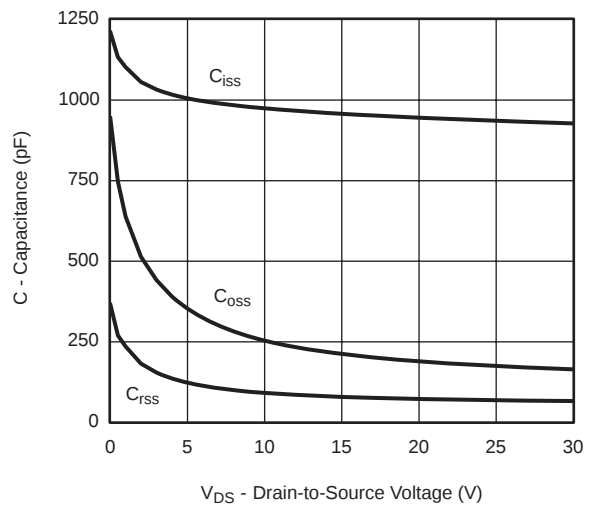
Output Characteristics



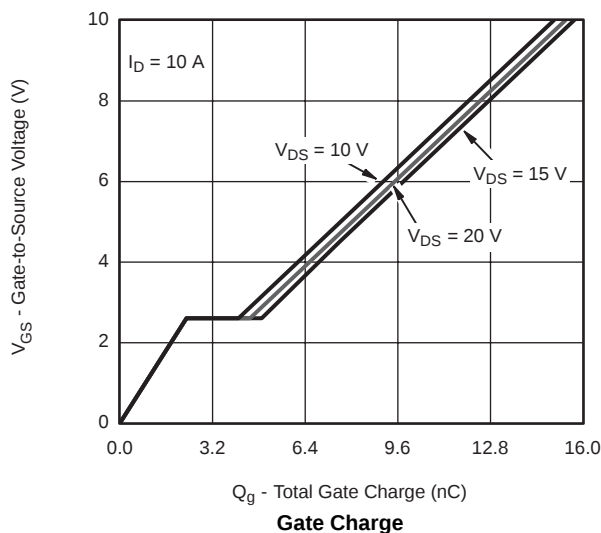
Transfer Characteristics



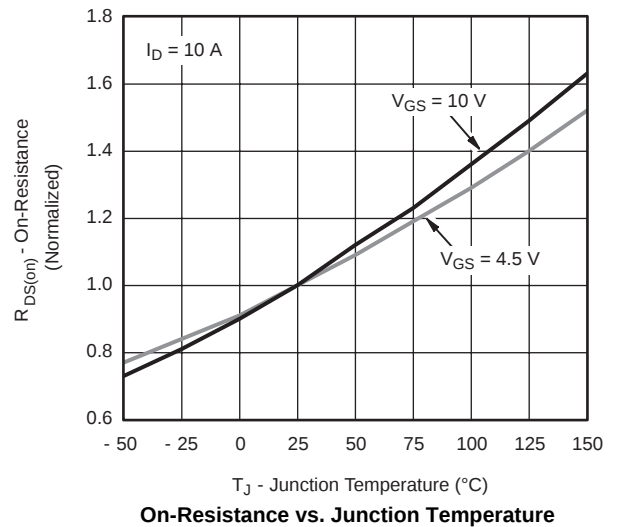
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

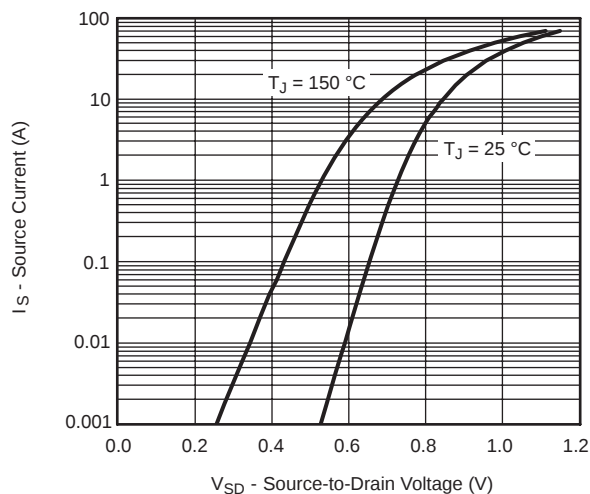


Gate Charge

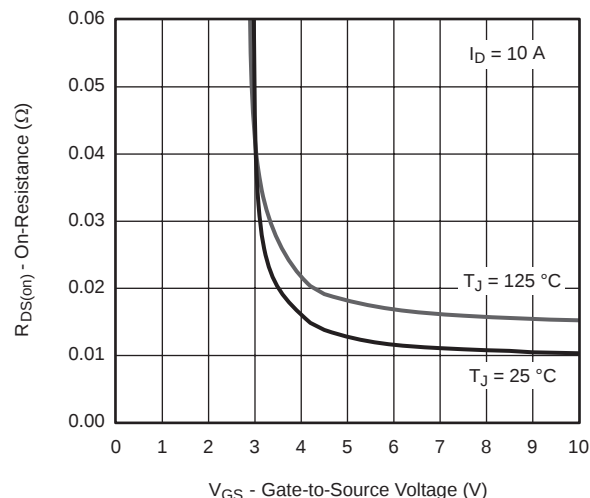


On-Resistance vs. Junction Temperature

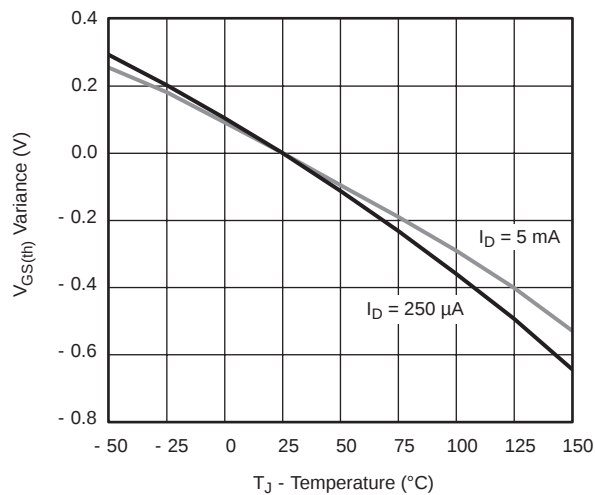
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



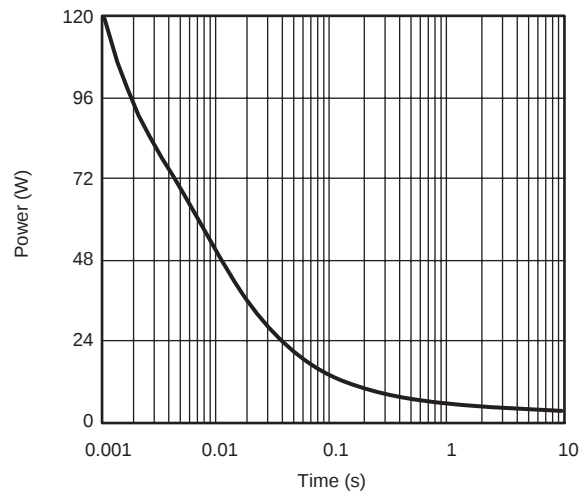
Source-Drain Diode Forward Voltage



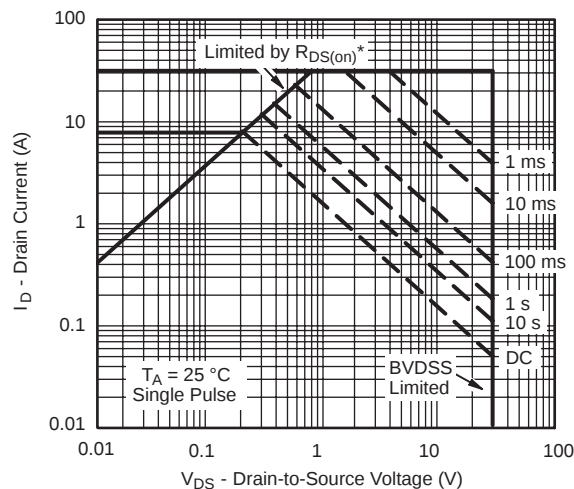
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



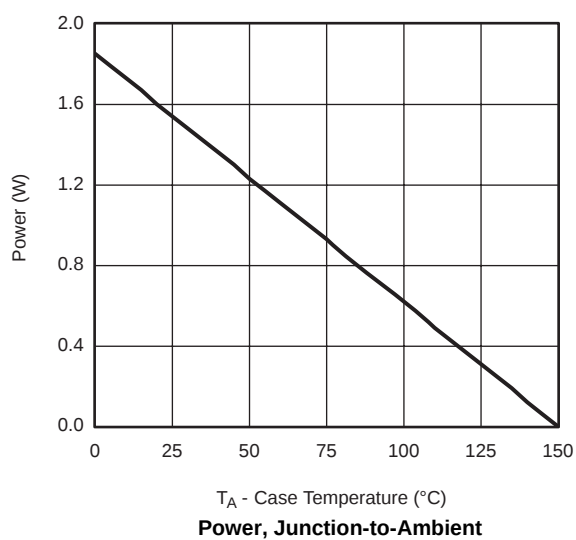
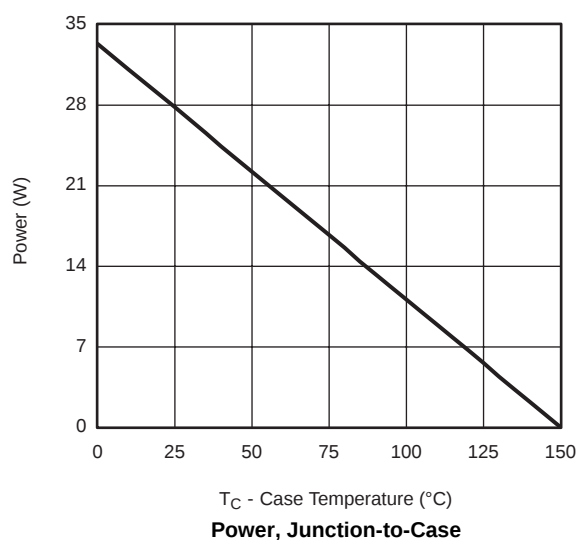
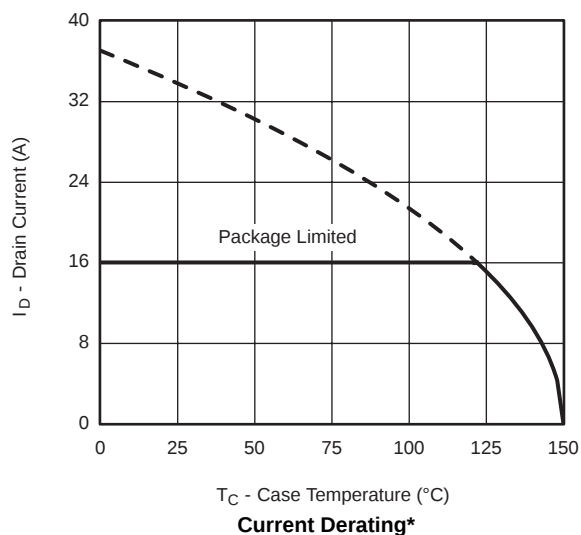
Single Pulse Power (Junction-to-Ambient)



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

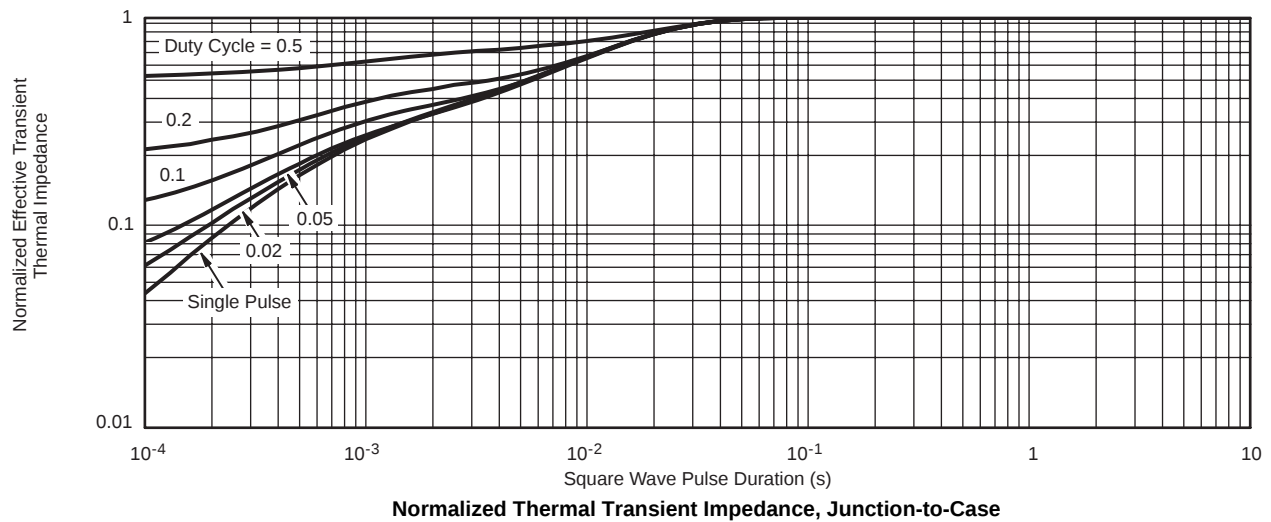
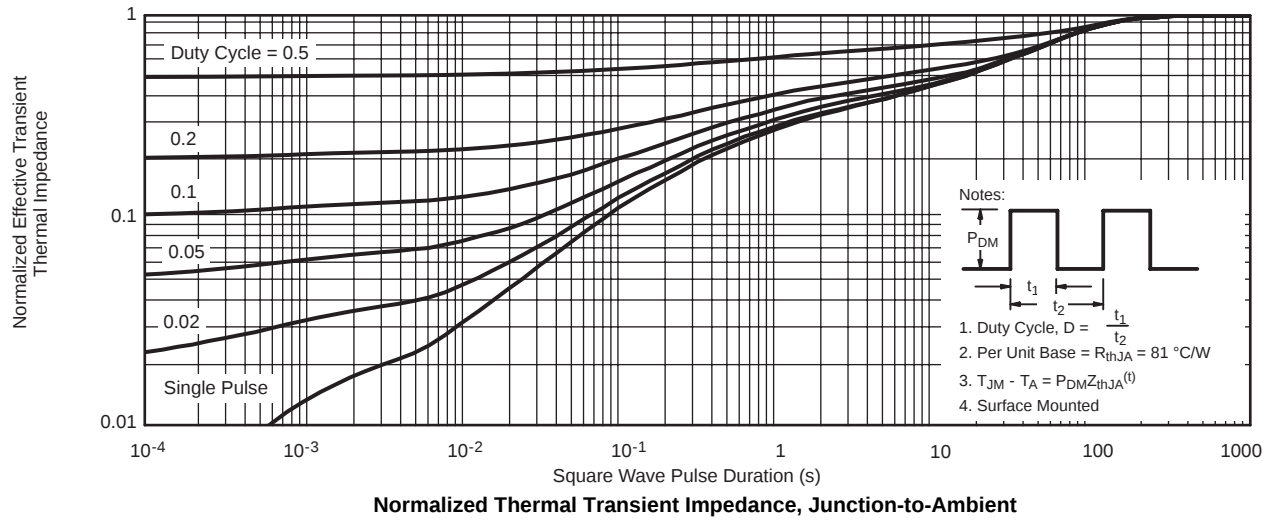
Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

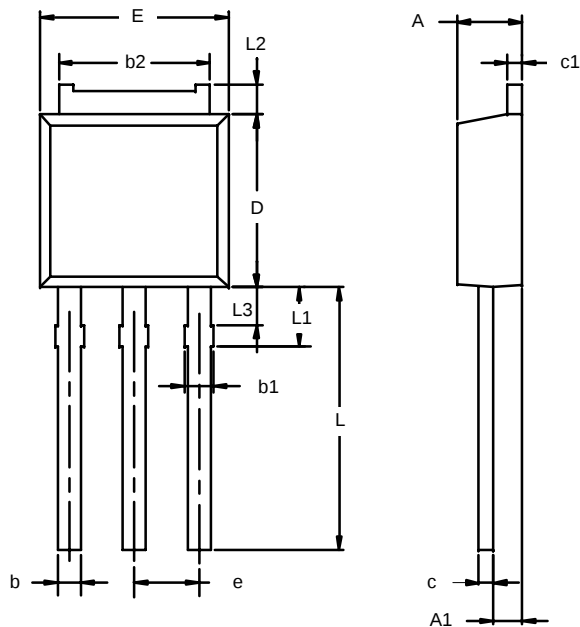


* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



TO-251AA (DPAK)



Note: Dimension L3 is for reference only.

Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	2.21	2.38	0.087	0.094
A1	0.89	1.14	0.035	0.045
b	0.71	0.89	0.028	0.035
b1	0.76	1.14	0.030	0.045
b2	5.23	5.43	0.206	0.214
c	0.46	0.58	0.018	0.023
c1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
E	6.48	6.73	0.255	0.265
e	2.28 BSC		0.090 BSC	
L	3.89	9.53	0.153	0.375
L1	1.91	2.28	0.075	0.090
L2	0.89	1.27	0.035	0.050
L3	1.15	1.52	0.045	0.060
ECN: S-03946—Rev. E, 09-Jul-01				
DWG: 5346				

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